



Silicon NPN Bipolar Transistor for Low-frequency Amplification
3DD5011AH

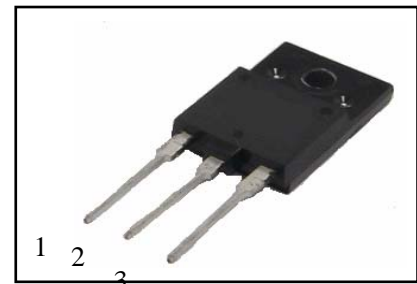
1 Description:

3DD5011AH, silicon NPN low frequency power transistor, is used to colour TV switching regulator.
 Package: TO-3P(H)IS.

Typical Data		
V _{CEO}	600	V
I _C	10	A
P _{tot} (T _C =25°C)	55	W

2 Characteristics:

- Low switching power dissipation
- Low reversing leaking current
- Good high-temperature characteristic
- Good current characteristic
- High reliability

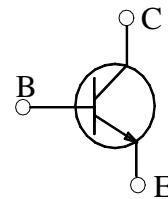


1. B 2. C 3. E

3 Application:

The device is mainly used in 14 and 21 inch colour TV switching regulator.

Equivalent circuit



The name and content of poisonous and harmful material in products

Part's Name	hazardous substance					
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE
CONTENT	≤0.1%	≤0.1%	≤0.01%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○
Molding Compound	○	○	○	○	○	○
Chip	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○
Solder	×	○	○	○	○	○
Note	○: means the hazardous material is under the criterion of SJ/T11363-2006. ×: means the hazardous material exceeds the criterion of SJ/T11363-2006. The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's ROHS.					

4 Electrical Characteristics

Maximum Ratings

Except for Other Prescription, $T_a = 25^\circ\text{C}$

Parameter Note		Symbol	Rating	Unit
Collector-Base Breakdown Voltage		V_{CB0}	900	V
Collector-Emitter Breakdown Voltage		V_{CEO}	600	V
Emitter-Base Breakdown Voltage		V_{EBO}	9	V
Collector Current		I_C	10	A
Power Dissipation	$T_a = 25^\circ\text{C}$	P_{tot}	2	W
	$T_c = 25^\circ\text{C}$		55	
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature		T_{stg}	-55~150	$^\circ\text{C}$

Electrical characteristics

Except for Other Prescription, $T_a = 25^\circ\text{C}$

Parameter Note	Symbol	Test Conditions	Criterion			Unit
			Min	Typ	Max	
Collector-Base Cutoff Current	I_{CBO}	$V_{CB} = 800\text{V}, I_E = 0$			10	μA
Collector- Emitter Cutoff Current	I_{CEO}	$V_{CE} = 600\text{V}, I_B = 0$			100	μA
Emitter-Base Cutoff Current	I_{EBO}	$V_{EB} = 9\text{V}, I_C = 0$			10	μA
Collector-Base Breakdown Voltage	V_{CB0}	$I_{CB} = 1\text{mA}, I_E = 0$	900			V
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_{CE} = 5\text{mA}, I_B = 0$	600			V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_{EB} = 1\text{mA}, I_C = 0$	9			V
DC Current Gain	h_{FE}^a	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	15		30	
Ratio Between h_{FE1} of Low Current and h_{FE2} of High Current	h_{FE1}	$h_{FE1}: V_{CE} = 5\text{V}, I_C = 5\text{A}$	6			
	h_{FE2}	$h_{FE2}: V_{CE} = 5\text{V}, I_C = 1\text{mA}$	10			
Collector-Emitter Saturation Voltage	$V_{CE\text{ sat}}^a$	$I_C = 4\text{A}, I_B = 0.8\text{A}$		0.25	1	V
Base-Emitter Saturation Voltage	$V_{BE\text{ sat}}^a$	$I_C = 4\text{A}, I_B = 0.8\text{A}$		0.88	1.5	V
Storage Time	t_s	UI9600, $I_C = 0.5\text{A}$		7.5	10	μs
Fall Time	t_f			0.6	1	μs
Transition Frequency	f_T	$V_{CE} = 10\text{V}, I_C = 0.1\text{A}$ $f = 0.3\text{MHz}$	4	12		MHz

a: Impulse $t_p \leq 300 \mu\text{s}, \delta \leq 2\%$

5 Typical Characteristics

Figure 1 Safe Operating Area

Figure2 Power Derating($P_{tot}-T$)

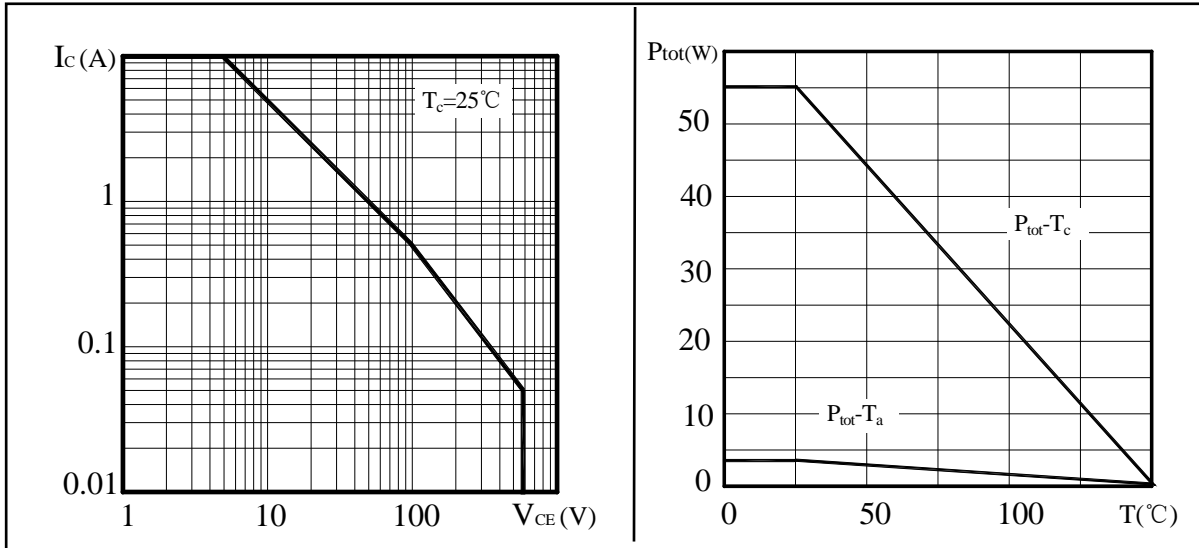


Figure 3 I_C-V_{CE} Characteristics(Typical)

Figure 4 $h_{FE}-I_C$ Characteristics(Typical)

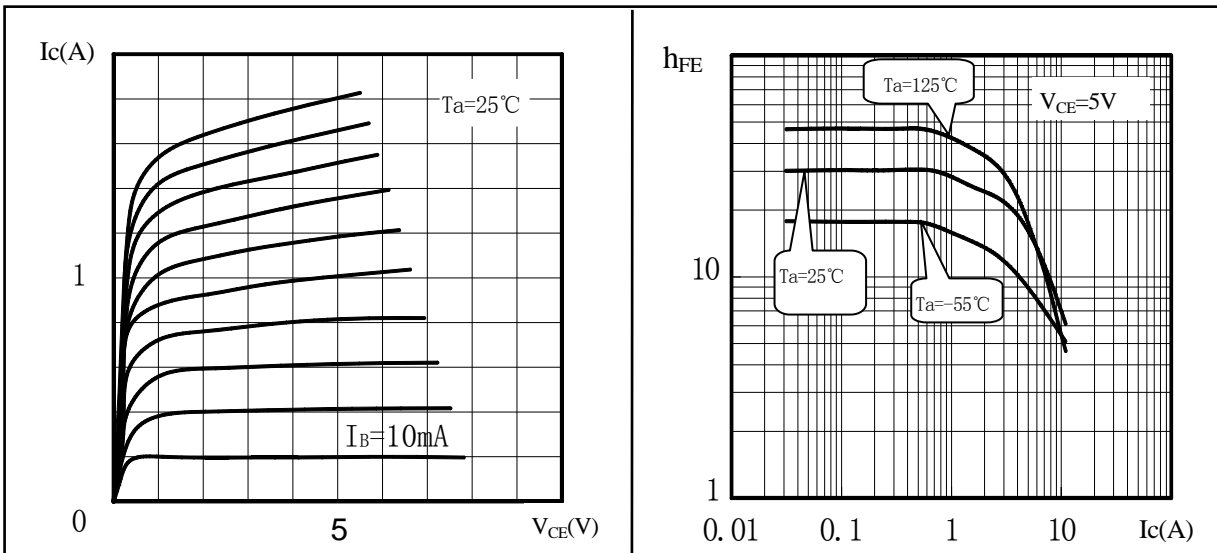


Figure 5 $V_{CE(sat)}$ - I_C Characteristics(Typical)

Figure 6 $V_{BE(sat)}$ - I_C Characteristics(Typical)

